

# Quiz-2

No Negative Marking. Duration - 15 mins.

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A dynamic random access memory does not use active devices to store information. 1 point

☐ True

☐ False

Match the columns:

4 points

	Poor noise margin	No current hogging	Current steering logic	Multi-emitter connection
ECL	<input type="radio"/>	<input type="radio"/>	<input type="radio"/>	<input type="radio"/>
TTL	<input type="radio"/>	<input type="radio"/>	<input type="radio"/>	<input type="radio"/>
RTL	<input type="radio"/>	<input type="radio"/>	<input type="radio"/>	<input type="radio"/>
IIL	<input type="radio"/>	<input type="radio"/>	<input type="radio"/>	<input type="radio"/>



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Which capacitance is considered as fan-out load?

1 point

- ☐ Cgb
- ☐ Cgs
- ☐ Cgd
- ☐ Csb

In the tri-state TTL circuit :

1 point

- ☐ The wired-AND operations are possible
- ☐ An Enable signal is used to switch between high impedance mode and normal logic operation mode
- ☐ When the Enable input is 'OFF', changes in the input signals do not affect the changes in the output
- ☐ All of these

Which of the following is not true in relation to TTL circuits ?

1 point

- ☐ The inputs are provided using a multi-emitter transistor
- ☐ The totem-pole TTL circuit supports a wired-AND implementation
- ☐ The open-collector TTL circuit supports a wired-AND implementation
- ☐ The typical Noise margin value associated with TTL circuits is 0.4 V



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Serial memories and random-access memories philosophically differ on account of: 1 point

- ☐ Memory Access Time
- ☐ Memory Size
- ☐ Memory Address Format
- ☐ None of these

For a memory architecture that has 16 blocks, with each block having 128 rows and 32 columns, the minimum number of bits required to define a typical memory location address is : 1 point

- ☐ 16
- ☐ 19
- ☐ 24
- ☐ 12

During a read operation in a 6T SRAM Cell – (BL in the bit-line) 1 point

- ☐ Both BL and BL' are pre-charged to VDD
- ☐ BL is pre-charged to VDD, and BL' is grounded
- ☐ BL' is pre-charged to VDD and BL' is grounded
- ☐ None of these



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In the 74S-series TTL ICs :

1 point

- ☐ Schottky transistors are used to improve the switching speed
- ☐ Schottky transistors are used to reduce the power consumption
- ☐ Schottky transistors are used to help the output transistors to enter into deep saturation
- ☐ All of these

In a 6 transistor SRAM design, if the power supply voltage is 1.8 V,  $V_T$  is 0.5 V,  $L_n$  is 0.18 microns and  $W_n$  is 0.27 microns, what can be said about the aspect ratio of the access transistors ?

1 point

- ☐  $(W/L)_a \leq 2.5$
- ☐  $(W/L)_a \leq 3$
- ☐  $(W/L)_a \geq 3$
- ☐  $(W/L)_a \geq 2.5$
- ☐ None of these

For 3 input CMOS NOR gate the worst-case pull-down size ratio is :

1 point

\_\_\_\_\_

- ☐  $3W/L$
- ☐  $2W/L$
- ☐  $W/L$
- ☐  $W/2L$



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The capacitive load calculation for transient analysis of 2 Input NAND Gate 1 point

- ☐ Does not consider all the intrinsic capacitor
- ☐ Consider only wire capacitance
- ☐ Consider all the intrinsic capacitors connected to power supply lines
- ☐ Do not consider the capacitors connected to power supply lines

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